

OPA5930UYO

Ultra Yellow LED Chip

Ultra Bright

GaAs/AlGaInP

1. Material Substrate GaAs (N Type)
Epitaxial Layer AlGaInP (P/N Type)

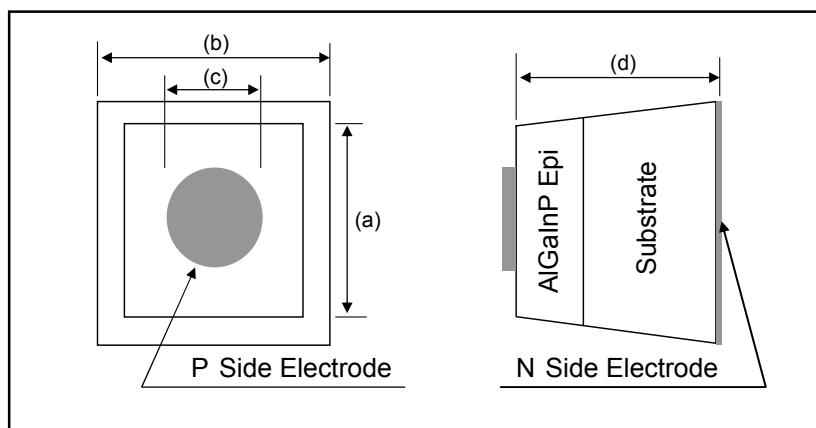
2. Electrode N(Cathode) Side Gold Alloy
P(Anode) Side Gold Alloy

3. Electro-Optical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	V_F		2.2	2.4	V	IF=20mA
Reverse Current	I_R			100	uA	VR=5V
Brightness	I_v	B	90	120	mcd	IF=20mA
		C	110	140		
		D	130	160		
		E	140	180		
		F	140	200		
		G	140	200		
Wavelength	λ_d		590		nm	IF=20mA
	$\Delta\lambda$		20		nm	IF=20mA

※ Note : Luminous Intensity is measured on bare chips.

4. Mechanical Data (a) Emission Area ----- 11mil x 11mil
(b) Bottom Area ----- 12mil x 12mil
(c) Bonding Pad ----- 100um
(d) Chip Thickness ----- 7mil

**AUK Corp.**

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